

MMJ65B0A02xx

2023/06/14

Features

Field Stop Trench gate IGBT、Low Collector-Emitter saturation voltage、High short circuit capability
Low switching losses

Version

Low Vcesat

Application

Industrial Motor Drivers, Inverter, Welding, UPS

Status

Mass production

Specifications

Gate-Emitter voltage V _{GES} [V]	Collector current I _C [A]	Collector- Emitter saturation voltage V _{CE(sat)} @T _j =25deg C typical limit	Collector- Emitter saturation voltage V _{CE(sat)} @T _j =25deg C upper limit	Gate Voltage V _{GES} [V]	Gate-Emitter threshold voltage V _{GE(th)} lower limit [V]	Gate-Emitter threshold voltage V _{GE(th)} upper limit [V]
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		[V]	[V]			
650	200	1.30	1.60	-30~30	5.00	6.80
Die size X [mm]		Die size Y [mm]		Junction temperature Tj [deg.C]		
10.60		10.60		-40~175		